

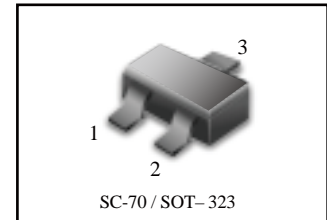
General Purpose Transistors PNP Silicon

● FEATURES

We declare that the material of product compliant with RoHS requirements and Halogen Free.

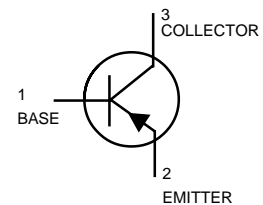
● DEVICE MARKING AND ORDERING INFORMATION

| Device | Marking | Shipping |
|---------|---------|----------------|
| 2N3906U | 2A | 3000/Tape&Reel |



● MAXIMUM RATINGS(Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|--------------------------------|------------------|--------|------|
| Collector–Emitter Voltage | V _{CEO} | -40 | Vdc |
| Collector–Base Voltage | V _{CB0} | -40 | Vdc |
| Emitter–Base Voltage | V _{EB0} | -5 | Vdc |
| Collector Current — Continuous | I _C | -200 | mAdc |



● THERMAL CHARACTERISTICS

| | | | |
|---|-----------------------------------|----------|------|
| Total Device Dissipation, (Note 1) @ T _A = 25°C | P _D | 150 | mW |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} | 833 | °C/W |
| Junction and Storage temperature | T _J , T _{stg} | -55~+150 | °C |

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.

● ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|--|----------------------|------|------|------|------|
| Collector–Emitter Breakdown Voltage(Note (I _C = -1.0 mAdc, I _B = 0) | V _{BR(CEO)} | -40 | - | - | V |
| Collector–Base Breakdown Voltage (I _C = -10 μAdc, I _E = 0) | V _{BR(CBO)} | -40 | - | - | V |
| Emitter–Base Breakdown Voltage (I _E = -10μAdc, I _C = 0) | V _{BR(EBO)} | -5 | - | - | V |
| Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0Vdc) | I _{CEX} | - | - | -50 | nA |
| Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0Vdc) | I _{BL} | - | - | -50 | nA |

2.Pulse Test: Pulse Width≤300 μs; Duty Cycle≤2.0%.

● ELECTRICAL CHARACTERISTICS (Ta= 25°C)(Continued)
ON CHARACTERISTICS (Note 1.)

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|---|----------------------|-----------------------------|-----------------------|-------------------------|------|
| DC Current Gain (I _C = -0.1 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -1.0 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -10 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -50 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -100 mA _{dc} , V _{CE} = -1.0 V _{dc}) | h _{FE} | 60 80 100 60 30 | – – – – – | – – 300 – – | |
| Collector–Emitter Saturation Voltage(3) (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50mA _{dc} , I _B = -5.0 mA _{dc}) | V _{CE(sat)} | – – | – – | -0.25 -0.4 | V |
| Base–Emitter Saturation Voltage (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50mA _{dc} , I _B = -5.0 mA _{dc}) | V _{BE(sat)} | -0.65 – | – – | -0.85 -0.95 | V |

SMALL–SIGNAL CHARACTERISTICS

| | | | | | |
|--|------------------|-----|---|-----|--------------------|
| Current–Gain — Bandwidth Product (I _C = -10mA _{dc} , V _{CE} = -20V _{dc} , f = 100MHz) | f _T | 250 | – | – | MHz |
| Output Capacitance (V _{CB} = -5.0 V _{dc} , I _E = 0, f = 1.0 MHz) | C _{obo} | – | – | 4.5 | pF |
| Input Capacitance (V _{EB} = -0.5 V _{dc} , I _C = 0, f = 1.0 MHz) | C _{ibo} | – | – | 10 | pF |
| Input Impedance (V _{CE} =-10 V _{dc} , I _C = -1.0 mA _{dc} , f = 1.0 kHz) | h _{ie} | 2 | – | 12 | k Ω |
| Voltage Feedback Ratio (V _{CE} = -10 V _{dc} , I _C = -1.0 mA _{dc} , f = 1.0 kHz) | h _{re} | 0.1 | – | 10 | X 10 ⁻⁴ |
| Small–Signal Current Gain (V _{CE} =-10 V _{dc} , I _C = -1.0 mA _{dc} , f = 1.0 kHz) | h _{fe} | 100 | – | 400 | |
| Output Admittance (V _{CE} =-10 V _{dc} , I _C =-1.0 mA _{dc} , f = 1.0 kHz) | h _{oe} | 3 | – | 60 | μmhos |
| Noise Figure (V _{CE} =-5V, I _C =-100μA, R _S =1.0kΩ, f =1.0kHz) | NF | – | – | 4 | dB |

SWITCHING CHARACTERISTICS

| | | | | | | |
|--------------|--|----------------|---|---|-----|----|
| Delay Time | (V _{CC} = -3.0 V _{dc} , V _{BE} = 0.5 V _{dc} , I _C = -10 mA _{dc} , I _{B1} = -1.0 mA _{dc}) | t _d | – | – | 35 | ns |
| Rise Time | | t _r | – | – | 35 | |
| Storage Time | | t _s | – | – | 225 | |
| Fall Time | | t _f | – | – | 75 | |

3.Pulse Test: Pulse Width ≤300 μs; Duty Cycle≤2.0%.

Electrical Characteristics Curves

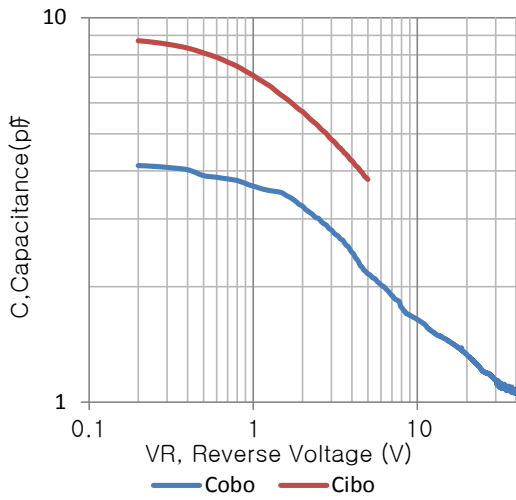


Figure 1. Capacitance

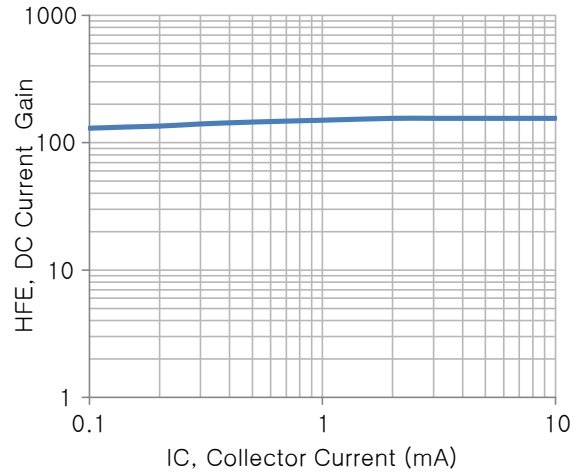


Figure 2. Current Gain

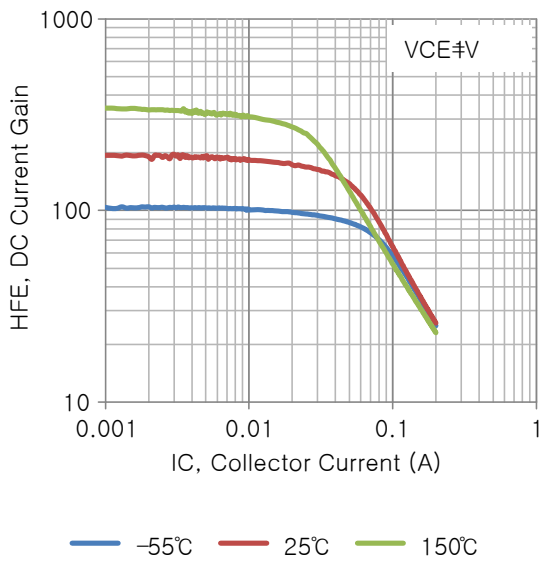


Figure 3. DC Current Gain

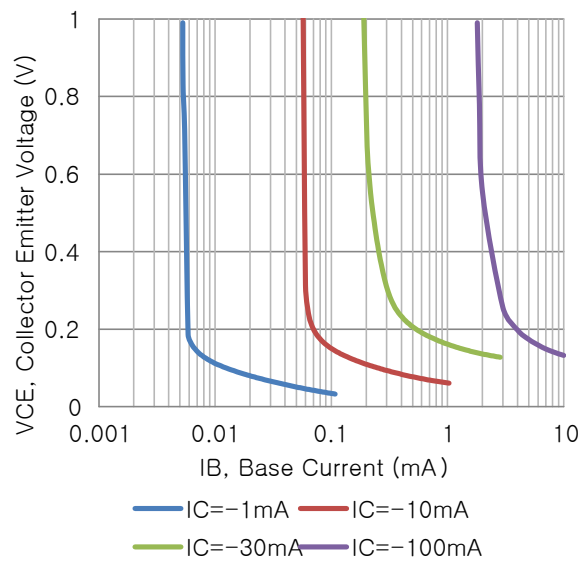


Figure 4. Collector Saturation Region

Electrical Characteristics Curves

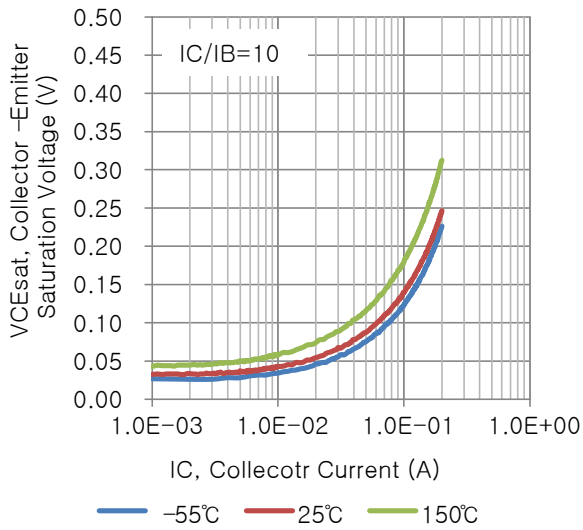


Figure 5. Collector Emitter Saturation Voltage vs. Collector Current

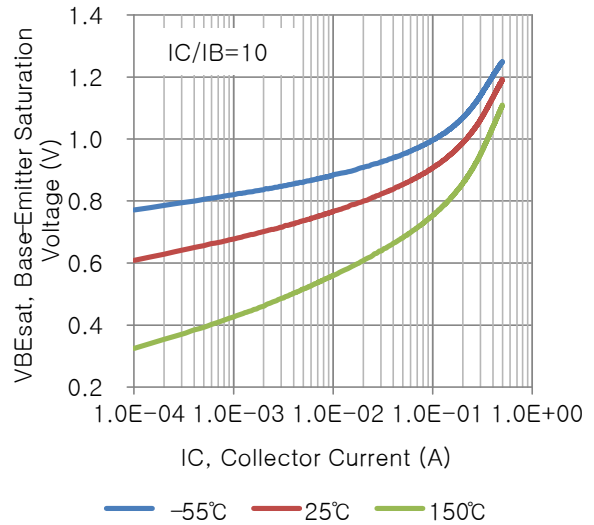


Figure 6. Base Emitter Saturation Voltage vs. Collector Current

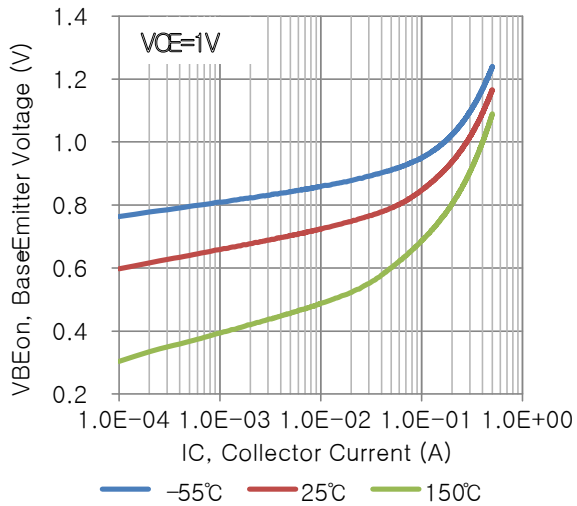
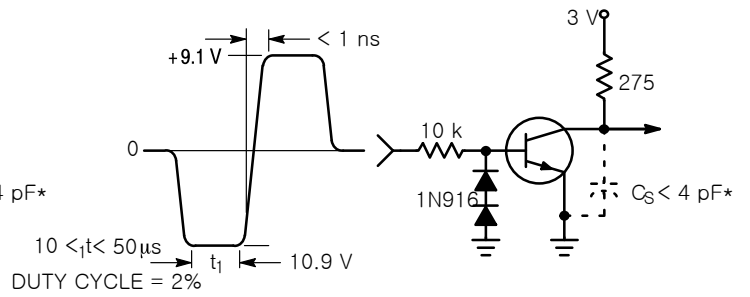
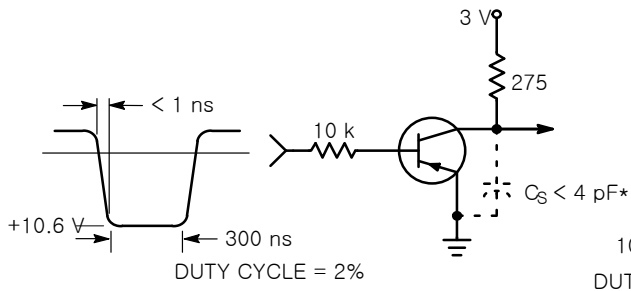


Figure 7. Base Emitter Voltage vs. Collector Current



* Total shunt capacitance of test jig and connectors

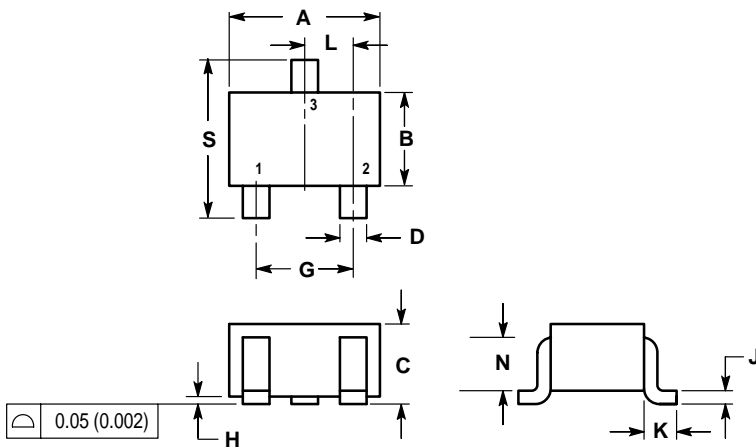
Figure 8. Delay and Rise Time Equivalent Test

Figure 9. Storage and Fall Time Equivalent Test

SC-70 / SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | 0.071 | 0.087 | 1.80 | 2.20 |
| B | 0.045 | 0.053 | 1.15 | 1.35 |
| C | 0.032 | 0.040 | 0.80 | 1.00 |
| D | 0.012 | 0.016 | 0.30 | 0.40 |
| G | 0.047 | 0.055 | 1.20 | 1.40 |
| H | 0.000 | 0.004 | 0.00 | 0.10 |
| J | 0.004 | 0.010 | 0.10 | 0.25 |
| K | 0.017 REF | | 0.425 REF | |
| L | 0.026 BSC | | 0.650 BSC | |
| N | 0.028 REF | | 0.700 REF | |
| S | 0.079 | 0.095 | 2.00 | 2.40 |

